

a¹ cont.
between at least two of said gate insulating films and provided on the surface of said semiconductor thin-film layer except for the areas just under said gate insulating films.

a²
32. (Amended) A thin-film semiconductor integrated circuit device, comprising a semiconductor thin-film layer provided at the upper part of an insulator and a plurality of insulated-gate semiconductor elements formed at said semiconductor thin-film layer, wherein a portion of said semiconductor thin-film layer located between said semiconductor elements is provided with a bottle-neck region of which cross-sectional area is smaller than that of other portions of said semiconductor thin-film layer.

Please add the following new claims to the application:

a³
--35. A thin-film semiconductor integrated circuit device as claimed in claim 30, wherein said seed crystal metal is selected from the group consisting of (a) metal M which is at least one of Se, Ti, V, Cr, Mn, Fe Co. Ni, Cu, Zn, Ru, Rh, Pd, Ag, Os, Ir, Pt, Au and alloys thereof, and (b) compound M_xA_y (where A is a Type IV-element, M is as set forth previously, and x and y are mixed crystal ratio of M and A).

36. A thin-film semiconductor device as claimed in claim 4, wherein said gate region includes a gate electrode, and said gate electrode is made of a metal.

37. A thin-film semiconductor device comprising an insulator, a semiconductor thin-film formed on said insulator and a transistor comprising a

a³
cont.

source region, a drain region, a channel region and a gate electrode formed at the surface of said semiconductor thin-film, said semiconductor thin-film having amorphous regions of Type-IV element and dendrite crystal regions of Type-IV element connecting said source region and said drain region, wherein said dendrite crystal regions are branching from one slender single crystal grain having {110} plane parallel to said substrate surface and {111} plane vertical to the major axis of the branch, said plurality of branches are joined with each other in any angle of 39.0°, 70.5° and 109.5°, and the joint surface thereof is {111} twin of Diamond structure.--
